POWERING AI

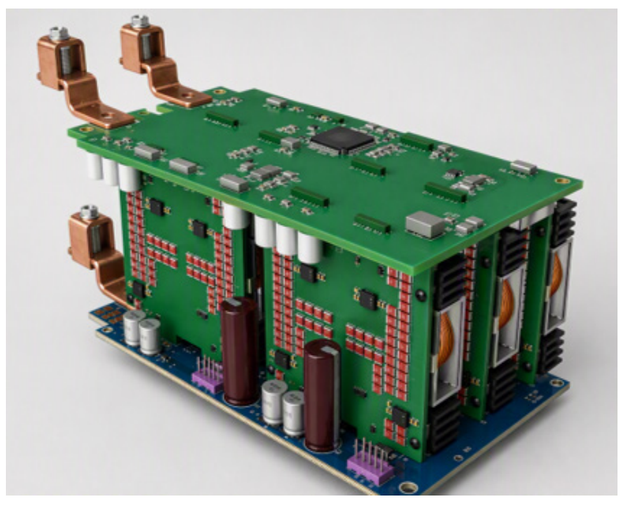
Energy backup for high-voltage AI data centers

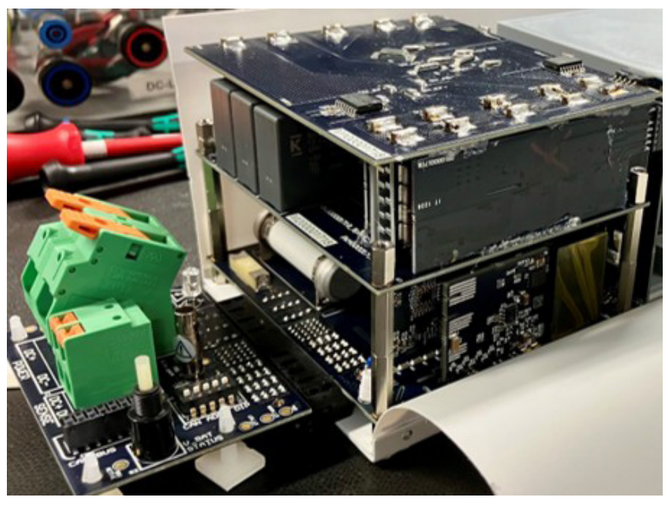
We offer a specialized combination of Si, SiC, and GaN semiconductor materials along with a special topology tailored to the battery backup requirements of high-voltage AI data centers. This innovative architecture enables ultra-high power densities of >600 W/in^3 for low-voltage BBUs and >300 W/in^3 for high-voltage BBUs, ensuring efficient, highly reliable, and uninterrupted operation.

Benefits
- Innovative, scalable design built on deep system understanding
- High power density: 625/332 W/in3 (LV/HV)
- High efficiency (> 98.5%) and scalability
- High reliability via multilevel topology with magnetic coupling (HV BBU)
- State-of-the-art topology with high power per phase (LV BBU)

Highlight products
- CoolGaN™ 100 V (LV)
- CoolSiC™ 650 V Gen2 MOSFET (HV)
- TLE497x sensors
- PSOC™ Performance line MCU
- CoolSET™ IC + 1.7 kV SiC MOSFET

Applications
- 25 kW 50 V battery backup units (BBUs)
- 24 kW 800 V BBUs





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